

Dual N-Ch 40V Fast Switching MOSFETs

Description

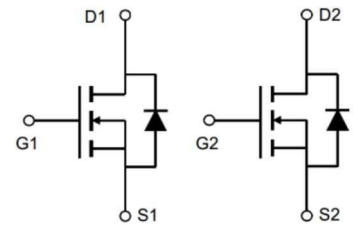
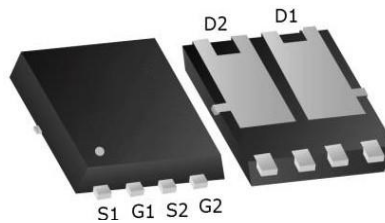
- ★ Advanced Trench MOS Technology
- ★ Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available

Product Summary

BVDSS	R _{DS(on)}	I _D
40V	13mΩ	33A

Applications

- ★ Power Management Functions.
- ★ DC-DC Converters.
- ★ Backlighting.

PDFN3X3 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	40	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	33	A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	21	A
I _{DM}	Pulsed Drain Current ²	55	A
EAS	Single Pulse Avalanche Energy ³	22.1	mJ
I _{AS}	Avalanche Current	10	A
P _D @T _C =25°C	Total Power Dissipation ⁴	31.3	W
P _D @T _A =25°C	Total Power Dissipation ⁴	2	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient (Steady State) ¹	---	60	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	5.5	°C/W

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Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

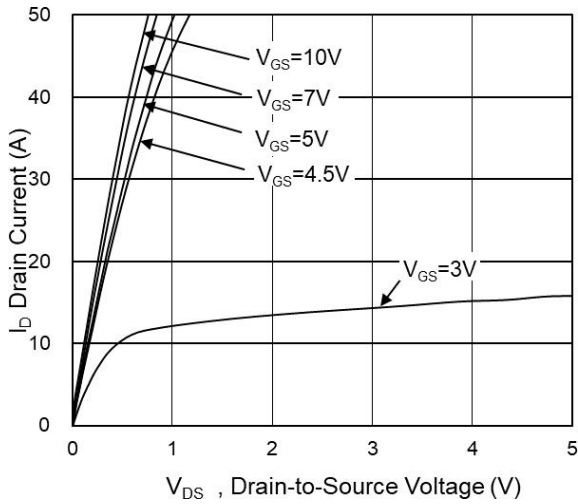
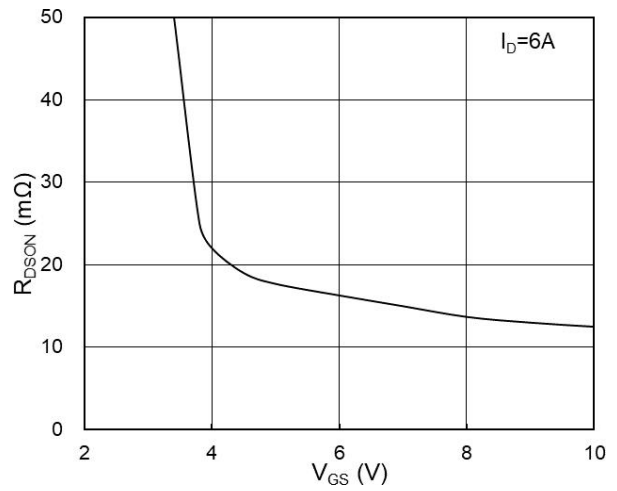
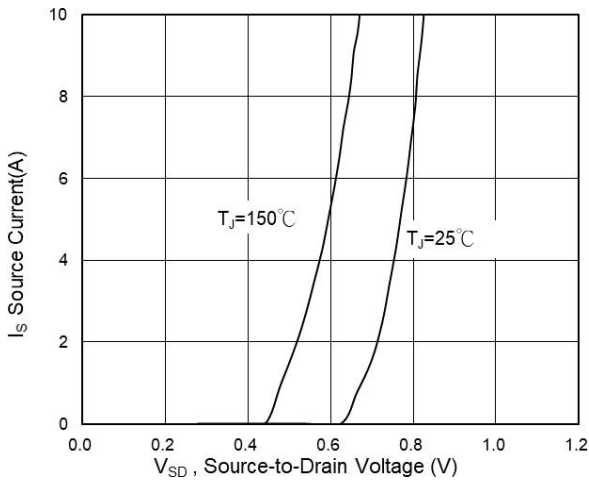
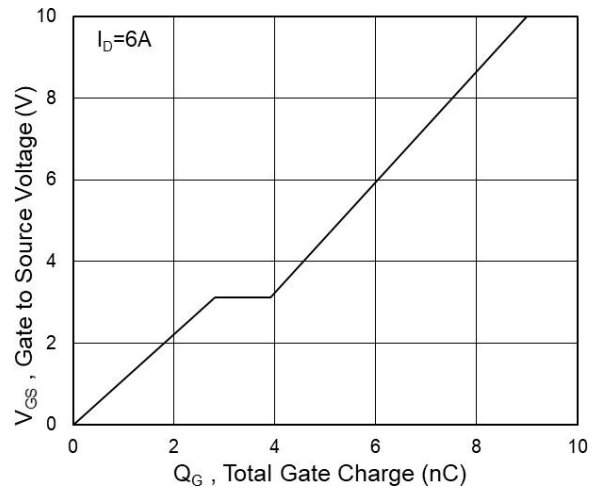
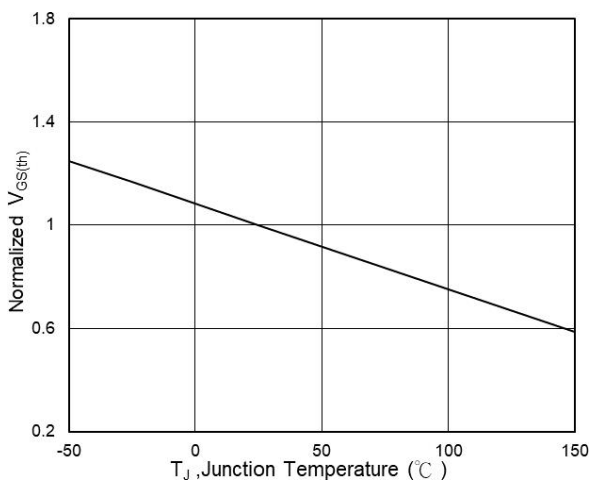
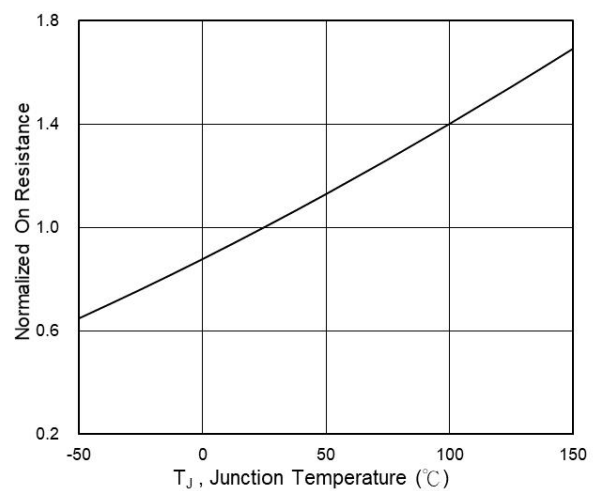
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=6A$	---	13	15	m Ω
		$V_{GS}=4.5V, I_D=5A$	---	19	23	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.7	2.4	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=32V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=32V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=12A$	---	30	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	2.1	---	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=32V, V_{GS}=4.5V, I_D=6A$	---	3.8	---	nC
Q_{gs}	Gate-Source Charge		---	2.8	---	
Q_{gd}	Gate-Drain Charge		---	1.1	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=20V, V_{GS}=10V, R_G=3.3\Omega$ $I_D=1A$	---	12.2	---	ns
T_r	Rise Time		---	5.3	---	
$T_{d(off)}$	Turn-Off Delay Time		---	18	---	
T_f	Fall Time		---	9	---	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	376	---	pF
C_{oss}	Output Capacitance		---	240	---	
C_{rss}	Reverse Transfer Capacitance		---	19	---	

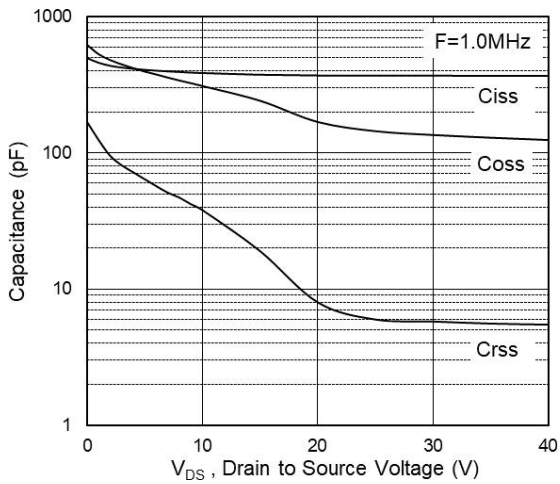
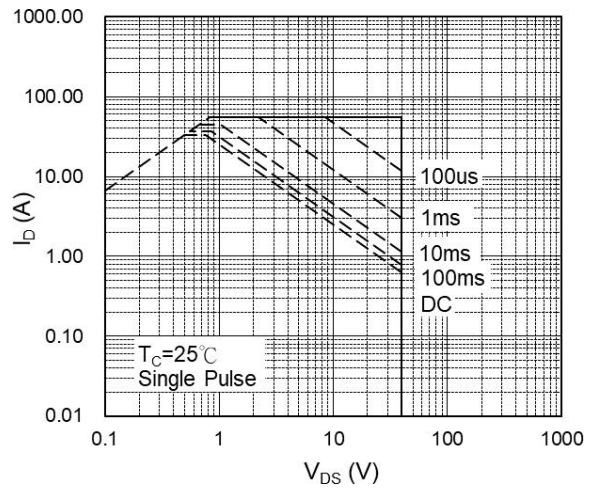
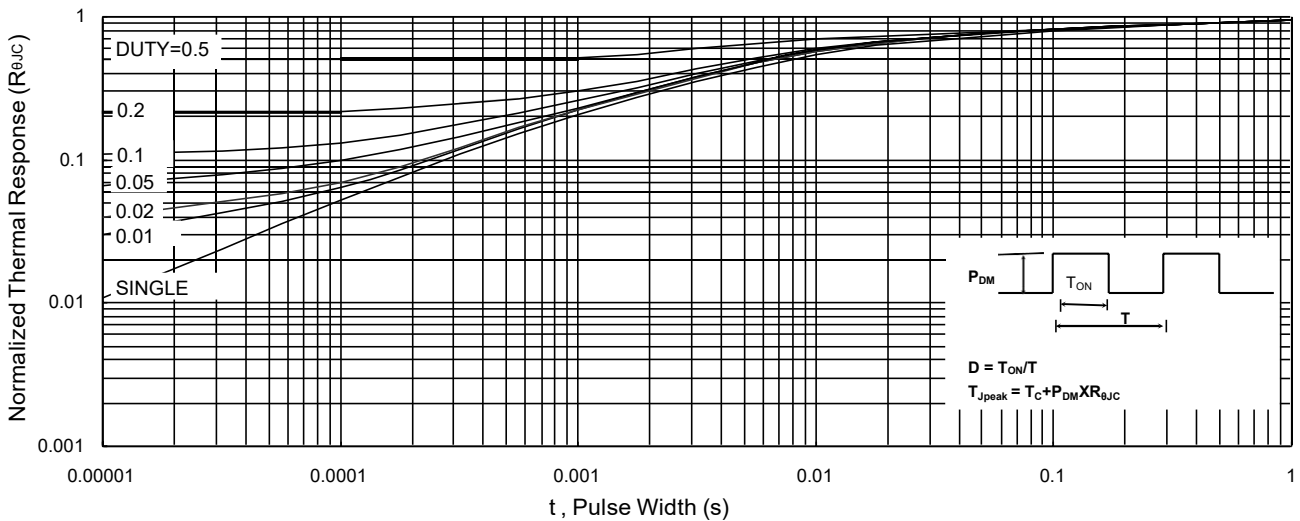
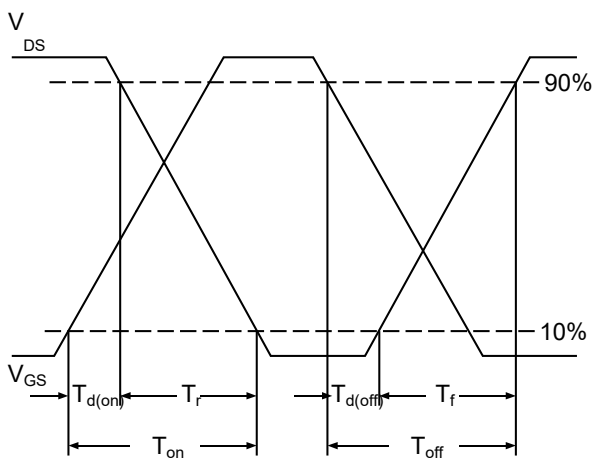
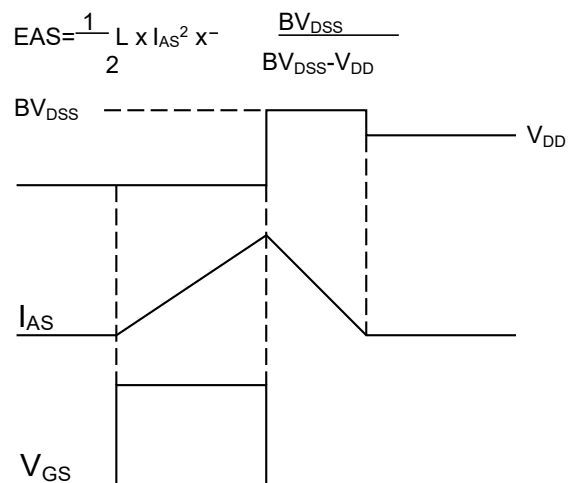
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	33	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=6A, dI/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	20	---	nS
Q_{rr}	Reverse Recovery Charge		---	35	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=10A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

Fig.1 Typical Output Characteristics

Fig.2 On-Resistance vs G-S Voltage

Fig.3 Source Drain Forward Characteristics

Fig.4 Gate-Charge Characteristics

Fig.5 Normalized $V_{GS(th)}$ vs T_J

Fig.6 Normalized $R_{DS(on)}$ vs T_J

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Fig.7 Capacitance

Fig.8 Safe Operating Area

Fig.9 Normalized Maximum Transient Thermal Impedance

Fig.10 Switching Time Waveform

Fig.11 Unclamped Inductive Switching Waveform

